



FQD2N60CTF Information



For Reference Only

Part Number FQD2N60CTF

 Manufacturer
 Fairchild/ON Semiconductor

 Category
 Discrete Semiconductor Products

 Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 1.9A DPAK **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQD2N60CTF Specifications

Manufacturer Part Number FQD2N60CTF Manufacturer Fairchild/ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 1.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 12nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 235pF @ 25V Vgs (Max) ±30pF @ 25V Vgs (Max) ±30pF @ 25V Vgs (Max) ±30pF @ 25V Vgs (Max) 4.7 Ohm @ 950mA, 10V Opearting Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C1.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds235pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 44W (Tc)Rds On (Max) @ Id, Vgs4.7 Ohm @ 950mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	FQD2N60CTF
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C1.9A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds235pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 44W (Tc)Rds On (Max) @ Id, Vgs4.7 Ohm @ 950mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	QFET?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 Ohm @ 950mA, 10V Operating Temperature Supplier Device Package Package / Case 1.9A (Tc) 1.9C (Tal) 1.9A (Tc) 1.9C (Tal) 1.9A (Tc) 1	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds235pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)2.5W (Ta), 44W (Tc)Rds On (Max) @ Id, Vgs4.7 Ohm @ 950mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Add Charge (Qg) (Max) @ Vds 235pF @ 25V	Current - Continuous Drain (Id) @ 25°C	1.9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 235pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 Ohm @ 950mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 235pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.7 Ohm @ 950mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 2.5W (Ta), 44W (Tc) Rds On (Max) @ Id, Vgs 4.7 Ohm @ 950mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
FET Feature - Power Dissipation (Max) 2.5W (Ta), 44W (Tc) Rds On (Max) @ Id, Vgs 4.7 Ohm @ 950mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	235pF @ 25V
Power Dissipation (Max) 2.5W (Ta), 44W (Tc) 4.7 Ohm @ 950mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs4.7 Ohm @ 950mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD-PakPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	2.5W (Ta), 44W (Tc)
Mounting Type Surface Mount Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	4.7 Ohm @ 950mA, 10V
Supplier Device Package D-Pak Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	D-Pak
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

FQD2N60CTF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQD2N60CTF Payment Methods



















FQD2N60CTF Shipping Methods













If you have any question about FQD2N60CTF, please do not hesitate to contact us!

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